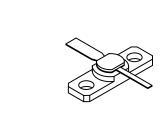
The RF Line Microwave Power Oscillator Transistor

 \dots designed for use as power oscillators at frequencies to 3.0 GHz with typical output power of over 1.0 watt.

- · Operation to 3.0 GHz
- High Output Power (1.2 W Typ @ 2.5 GHz)
- Rugged Capable of Withstanding High Load VSWR
- High Reliability
- · Hermetic Package
- · Gold Metallization
- · Diffused Emitter Ballast Resistors
- Common Collector Configuration
- Formerly named TRW62601
- Circuit board photomaster available upon request by contacting RF Tactical Marketing in Phoenix, AZ.

TP62601

MICROWAVE POWER OSCILLATOR TRANSISTOR



CASE 328A-03, STYLE 3 (GP-13)

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCEO	22	Vdc
Collector–Base Voltage	V _{CBO}	45	Vdc
Emitter–Base Voltage	V _{EBO}	3.5	Vdc
Collector Current — Continuous	l _C	0.5	Adc
Operating Junction Temperature	TJ	200	°C
Storage Temperature Range	T _{stg}	-65 to +200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	15	°C/W

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Тур	Max	Unit		
OFF CHARACTERISTICS							
Collector–Emitter Breakdown Voltage (I _C = 20 mA, I _B = 0)	V(BR)CEO	22	_	_	Vdc		
Collector–Base Breakdown Voltage (I _C = 1.0 mA, I _E = 0)	V(BR)CBO	45	_	_	Vdc		
Emitter–Base Breakdown Voltage ($I_E = 0.25 \text{ mA}, I_C = 0$)	V(BR)EBO	3.5	_	_	Vdc		
Collector–Emitter Breakdown Voltage (I_C = 20 mA, R_{BE} = 10 Ω)	V(BR)CER	50	_	_	Vdc		
Collector Cutoff Current (V _{CB} = 28 V, I _E = 0)	ІСВО		_	0.125	mAdc		

ON CHARACTERISTICS

ON CHARACTERISTICS					
DC Current Gain ($I_C = 100 \text{ mA}, V_{CE} = 5.0 \text{ V}$)	hFE	20	_	120	_

(continued)





ELECTRICAL CHARACTERISTICS — continued

Characteristic	Symbol	Min	Тур	Max	Unit		
DYNAMIC CHARACTERISTICS		•					
Output Capacitance (V _{CB} = 28 V, I _E = 0, f = 1.0 MHz)	C _{ob}	_	_	5.0	pF		
FUNCTIONAL TESTS							
Oscillator Output Power (V _{CE} = 20 V, f = 2.0 GHz, I _E = 220 mA)	P _{out}	1.25	_	_	W		
Load Mismatch (V _{CE} = 20 V, I _E = 220 mA, P _{OUt} = 1.25 W, f = 2.0 GHz, Load VSWR = ∞ :1, All Phase Angles)	Ψ	No	No Degradation in Output Power				
Cutoff Frequency (V _{CF} = 20 V, I _F = 220 mA)	f_{τ}	_	2.7	_	GHz		

TYPICAL CHARACTERISTICS

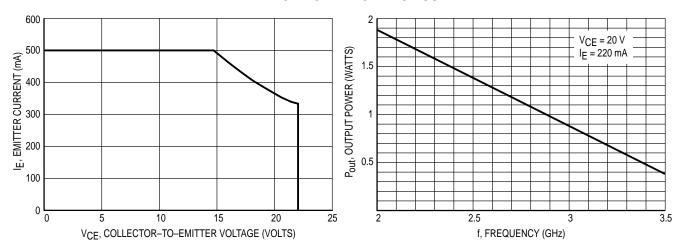


Figure 1. DC Safe Operating Area

Figure 2. Output Power versus Frequency

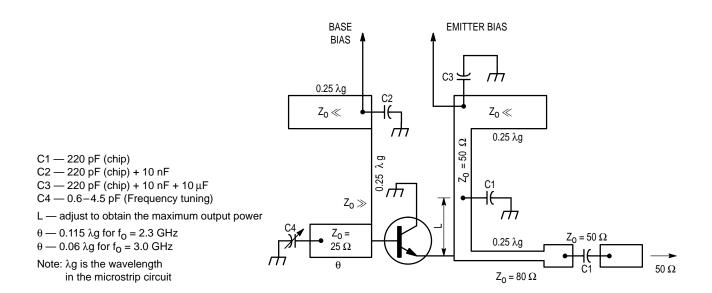


Figure 3. Test Circuit

TYPICAL CHARACTERISTICS

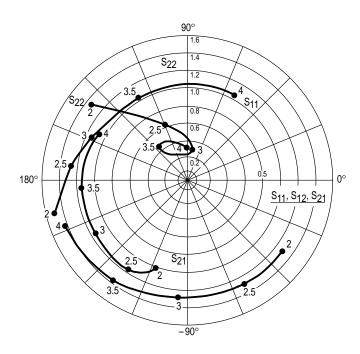
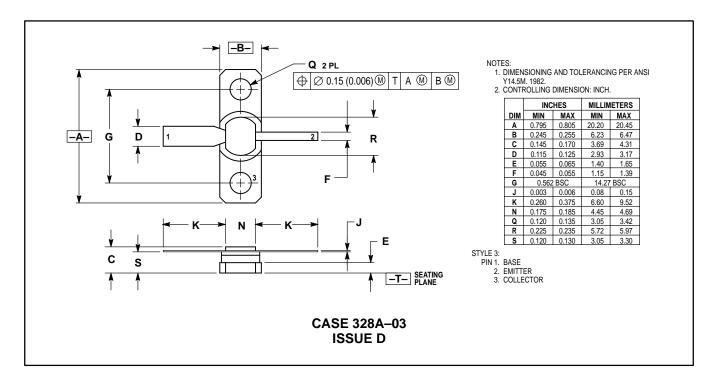


Figure 4. Small Signal S-Parameters (V_{CE} = 20 V, I_E = 220 mA)

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